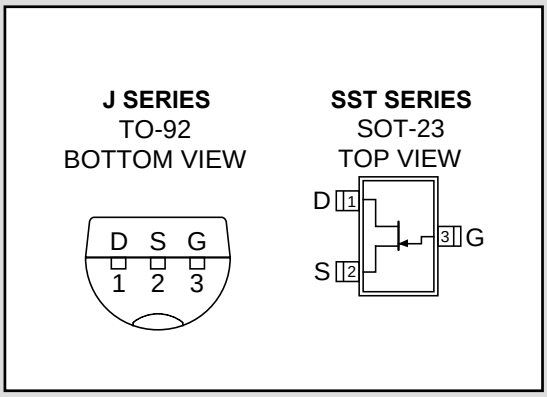
LINEAR SYSTEMS

Linear Integrated Systems

J/SST201 SERIES

HIGH GAIN N-CHANNEL JFET

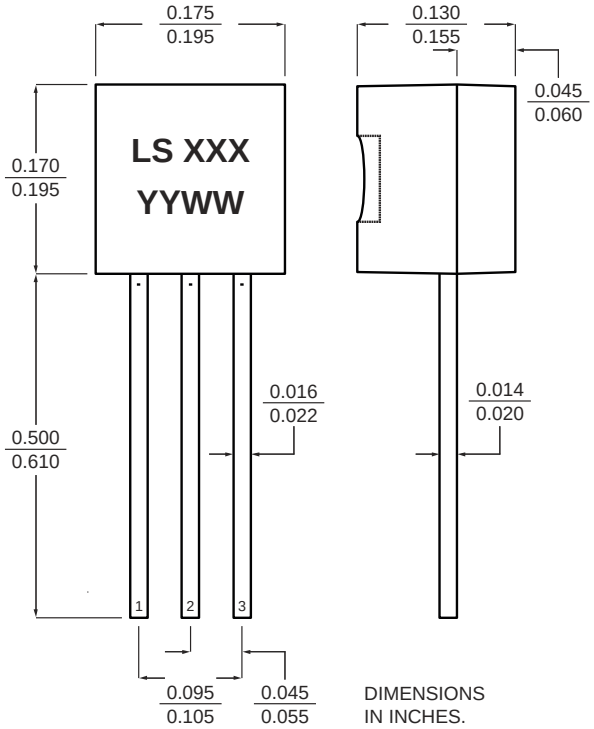
FEATURES	
DIRECT REPLACEMENT FOR SILICONIX J/SST201 SERIES	
LOW CUTOFF VOLTAGE	$V_{GS(off)} \leq 1.5V$
HIGH GAIN	A_V = 80 V/V
ABSOLUTE MAXIMUM RATINGS[1] @ 25 °C (unless otherwise stated)	
Maximum Temperatures	
Storage Temperature	-65 to +150 °C
Operating Junction Temperature	-55 to +135 °C
Maximum Power Dissipation	
Continuous Power Dissipation	350mW
Maximum Current	
Forward Gate Current	50mA
Maximum Voltages	
Gate to Drain Voltage	-40V
Gate to Source Voltage	-40V



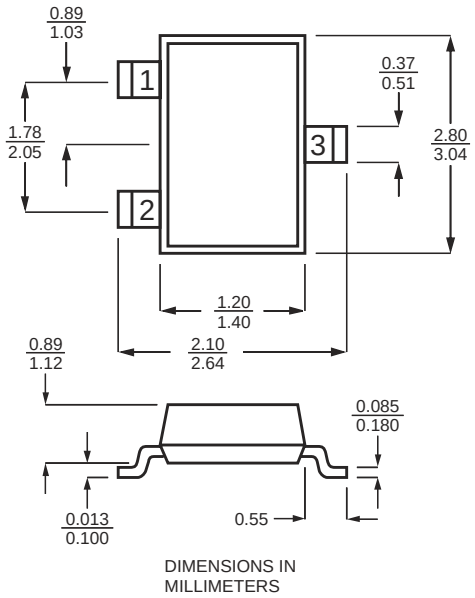
ELECTRICAL CHARACTERISTICS @ 25 °C (unless otherwise stated)

SYMBOL	CHARACTERISTIC		MIN	TYP	MAX	UNITS	CONDITIONS
BV_{GSS}	Gate to Source Breakdown Voltage	J/SST201, 202	-40			V	I_G = -1µA, V_{DS} = 0V
		J/SST204	-25				
$V_{GS(off)}$	Gate to Source Cutoff Voltage	J/SST201	-0.3		-1.5		V_{DS} = 15V, I_D = 10nA
		J/SST202	-0.8		-4		
		J/SST204	-0.3		2		
I_{DSS}	Drain to Source Saturation Current[2]	J/SST201	0.2		1	mA	V_{DS} = 15V, V_{GS} = 0V
		J/SST202	0.9		4.5		
		J/SST204	0.2		3		
I_{GSS}	Gate Reverse Current		-2		-100	pA	V_{GS} = -20V, V_{DS} = 0V
I_G	Gate Operating Current			-2			V_{DG} = 10V, I_D = 0.1mA
$I_{D(off)}$	Drain Cutoff Current			2			V_{DS} = 15V, V_{GS} = -5V
g_{fs}	Forward Transconductance	J/SST201, 204	0.5			mS	V_{DS} = 15V, V_{GS} = 0V, *f* = 1kHz
		J/SST202	1				
C_{iss}	Input Capacitance			4.5		pF	V_{DS} = 15V, V_{GS} = 0V, *f* = 1MHz
C_{rss}	Reverse Transfer Capacitance			1.3			
e_n	Noise Voltage			6		nV/√Hz	V_{DS} = 10V, V_{GS} = 0V, *f* = 1kHz

TO-92



SOT-23



1. Absolute maximum ratings are limiting values above which serviceability may be impaired.
2. Pulse Test: PW ≤ 300μs, Duty Cycle ≤ 3%